ELECTRONICS, INC.
44 FARRAND STREET
BLOOMFIELD, NJ 07003
(973) 748–5089

NTE2543
Silicon NPN Transistor
Darlington, Motor/Relay Driver

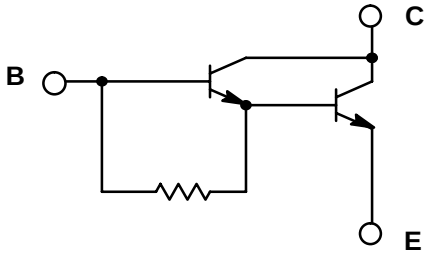
Absolute Maximum Ratings:

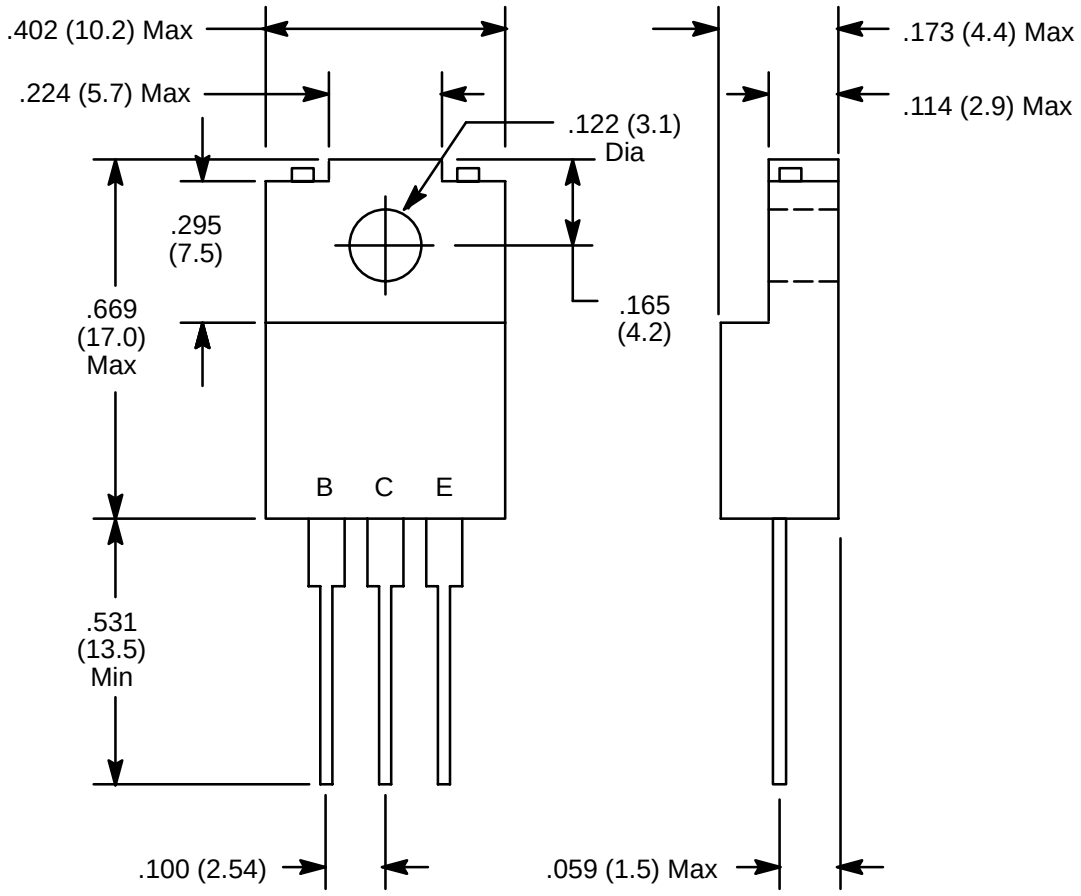
Collector Base Voltage, V_{CBO} 300V
Collector Emitter Voltage, V_{CEO} 250V
Emitter Base Voltage, V_{EBO} 20V
Collector Current, I_C 6A
Base Current. I_B 1A
Collector Power Dissipation (T_{FL} = +25°C), P_C 40W
Operating Junction Temperature, T_J . . . . . +150°C
Storage Temperature Range, T_{stg} . . . . . –55° to +150°C

Electrical Characteristics:

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	V_{CB} = 300V, I_E = 0	–	–	100	μA
Emitter Cutoff Current	I_{EBO}	V_{EB} = 20V, I_C = 0	–	–	10	mA
Collector–Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C = 25mA, R_{BE} = ∞	250	–	–	V
DC Current Gain	h_{FE}	V_{CE} = 2V, I_C = 2A	2000	–	–	
Collector–Emitter Saturation Voltage	$V_{CE(sat)}$	I_C = 2A, I_B = 2mA	–	–	1.5	V
Base–Emitter Saturation Voltage	$V_{BE(sat)}$	I_C = 2A, I_B = 2mA	–	–	2.0	V

Schematic Diagram





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